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SHEET 1 OF 4

FORM PTO - 1449

SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENT

APR 07 2005

ATTORNEY DOCKET NO.: ASC-025DV2C1

APPLICANT(S): Cheng *et al.*

SERIAL NO.: 10/802,186

FILING DATE: March 17, 2004

GROUP: 2813

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>SFL</i>	A254	2002/0063292	05/30/2002	Armstrong <i>et al.</i>			
	A255	2002/0190284	12/19/2002	Murthy <i>et al.</i>			
	A256	2004/0007724	01/15/2004	Murthy <i>et al.</i>			
	A257	2004/0014276	01/22/2004	Murthy <i>et al.</i>			
	A258	2004/0070035	04/15/2004	Murthy <i>et al.</i>			
	A259	2004/0084735	05/06/2004	Murthy <i>et al.</i>			
	A260	2004/0119101	06/24/2004	Schrom <i>et al.</i>			
	A261	2004/0142545	07/22/2004	Ngo <i>et al.</i>			
	A262	2004/0173815	09/09/2004	Yeo <i>et al.</i>			
	A263	5,089,872	02/18/1992	Ozturk <i>et al.</i>			
	A264	5,242,847	09/07/1993	Ozturk <i>et al.</i>			
	A265	6,228,694	05/08/2001	Doyle <i>et al.</i>			
	A266	6,235,568	05/22/2001	Murthy <i>et al.</i>			
	A267	6,281,532	08/28/2001	Doyle <i>et al.</i>			
	A268	6,326,664	12/04/2001	Chau <i>et al.</i>			
	A269	6,563,152	05/13/2003	Roberds <i>et al.</i>			
	A270	6,605,498	08/12/2003	Murthy <i>et al.</i>			
	A271	6,621,131	09/16/2003	Murthy <i>et al.</i>			
	A272	6,657,223	12/02/2003	Wang <i>et al.</i>			
	A273	6,703,648	03/09/2004	Xiang <i>et al.</i>			
✓	A274	6,743,684	06/01/2004	Liu			

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3/02/07

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FOREIGN PATENT DOCUMENTS

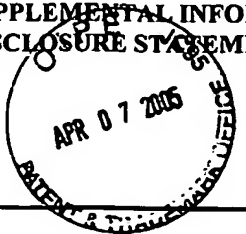
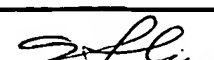
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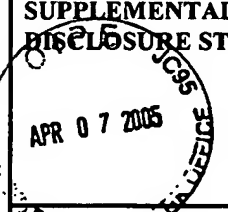
OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)							
	C145	Gannavaram, <i>et al.</i> , "Low Temperature ($\leq 800^{\circ}\text{C}$) Recessed Junction Selective Silicon-Germanium Source/Drain Technology for sub-70 nm CMOS," <u>IEEE International Electron Device Meeting Technical Digest</u> , (2000), pp. 437-440.						
	C146	Ge <i>et al.</i> , "Process-Strained Si (PSS) CMOS Technology Featuring 3D Strain Engineering," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2003) pp. 73-76.						
	C147	Ghani <i>et al.</i> , "A 90nm High Volume Manufacturing Logic Technology Featuring Novel 45nm Gate Length Strained Silicon CMOS Transistors," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2003), 978-980.						
	C148	Hamada <i>et al.</i> , "A New Aspect of Mechanical Stress Effects in Scaled MOS Devices," <u>IEEE Transactions on Electron Devices</u> , Vol. 38, No. 4 (April 1991), pp. 895-900.						
	C149	Huang <i>et al.</i> , "Isolation Process Dependence of Channel Mobility in Thin-Film SOI Devices," <u>IEEE Electron Device Letters</u> , Vol. 17, No. 6 (June 1996), pp. 291-293.						
	C150	Huang <i>et al.</i> , "LOCOS-Induced Stress Effects on Thin-Film SOI Devices," <u>IEEE Transactions on Electron Devices</u> , Vol. 44, No. 4 (April 1997), pp. 646-650.						
	C151	Huang, <i>et al.</i> , "Reduction of Source/Drain Series Resistance and Its Impact on Device Performance for PMOS Transistors with Raised $\text{Si}_{1-x}\text{Ge}_x$ Source/Drain", <u>IEEE Electron Device Letters</u> , Vol. 21, No. 9, (Sept. 2000) pp. 448-450.						
	C152	Iida <i>et al.</i> , "Thermal behavior of residual strain in silicon-on-insulator bonded wafer and effects on electron mobility," <u>Solid-State Electronics</u> , Vol. 43 (1999), pp. 1117-1120.						

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FORM PTO - 1449				ATTORNEY DOCKET NO.: ASC-025DV2C1					
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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
	C153	Ito <i>et al.</i> , "Mechanical Stress Effect on Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2000), pp. 247-250.							
	C154	Lochtefeld <i>et al.</i> , "Investigating the Relationship Between Electron Mobility and Velocity in Deeply Scaled NMOS via Mechanical Stress," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 12 (2001), pp. 591-593.							
	C155	Ootsuka <i>et al.</i> , "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Applications," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2000), pp. 575-578.							
	C156	Ota <i>et al.</i> , "Novel Locally Strained Channel Technique for High Performance 55nm CMOS," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2002), pp. 27-30.							
	C157	Öztürk, <i>et al.</i> , "Advanced Si _{1-x} Ge _x Source/Drain and Contact Technologies for Sub-70 nm CMOS," <u>IEEE International Electron Device Meeting Technical Digest</u> , (2002), pp. 375-378.							
	C158	Öztürk, <i>et al.</i> , "Low Resistivity Nickel Germanosilicide Contacts to Ultra-Shallow Si _{1-x} Ge _x Source/Drain Junctions for Nanoscale CMOS," <u>IEEE International Electron Device Meeting Technical Digest</u> (2003), pp. 497-500.							
	C159	Öztürk, <i>et al.</i> , "Selective Silicon-Germanium Source/Drain Technology for Nanoscale CMOS," <u>Mat. Res. Soc. Symp. Proc.</u> , Vol. 717, (2002), pp. C4.1.1-C4.1.12.							
	C160	Öztürk, <i>et al.</i> , "Ultra-Shallow Source/Drain Junctions for Nanoscale CMOS Using Selective Silicon-Germanium Technology," <u>Extended Abstracts of International Workshop on Junction Technology</u> , (2001), pp. 77-82.							
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FORM PTO - 1449				ATTORNEY DOCKET NO.: ASC-025DV2C1					
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Cheng <i>et al.</i>					
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OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
	C161	Shimizu <i>et al.</i> , "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2001), pp. 433-436.							
	C162	Thompson <i>et al.</i> , "A Logic Nanotechnology Featuring Strained-Silicon," <u>IEEE Electron Device Letters</u> , Vol. 25, No. 4 (April 2004), pp. 191-193.							
	C163	Thompson <i>et al.</i> , "A 90 nm Logic Technology Featuring 50nm Strained-Silicon Channel Transistors, 7 layers of Cu Interconnects, Low k ILD, and 1um ² SRAM Cell," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (2002), pp. 61-64.							
	C164	Tiwari <i>et al.</i> , "Hole Mobility Improvement in Silicon-on-Insulator and Bulk Silicon Transistors Using Local Strain," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (1997), pp. 939-941.							
	C165	Uchino, <i>et al.</i> , "A Raised Source/Drain Technology Using In-situ P-doped SiGe and B-doped Si for 0.1-μm CMOS ULSIs," <u>IEEE International Electron Device Meeting Technical Digest</u> , (1997), pp. 479-482.							
EXAMINER	<i>S. J. Lu</i>				DATE CONSIDERED <i>3/2/07</i>				

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EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>SP</i>	A251	5,091,767	02/25/1992	Bean, <i>et al.</i>		
<i>SP</i>	A252	5,923,046	07/13/1999	Tezuka <i>et al.</i>		
<i>SP</i>	A253	6,828,214 B2	12/07/2004	Notsu, <i>et al.</i>		04/02/2002

FOREIGN PATENT DOCUMENTS

EXAM. INIT.	DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>SP</i>	B48	6-244112	09/02/1994	JP			Y	Y
<i>SP</i>	B49	9-219524	08/19/1997	JP			N	Y (Abstract only)

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)
<i>SP</i>	C103 Batterman, "Hillocks, Pits, and Etch Rate in Germanium Crystals," <u>Journal of Applied Physics</u> , Vol. 28, No. 11 (November, 1957), pp. 1236-1241.
<i>SP</i>	C104 Bohg, "Ethylene Diamine-Pyrocatechol-Water Mixture Shows Etching Anomaly in Boron-Doped Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 118, No. 2 (February 1971), pp. 401-402.
<i>SP</i>	C105 Brunner <i>et al.</i> , "Molecular beam epitaxy growth and thermal stability of Si _{1-x} Ge _x layers on extremely thin silicon-on-insulator substrates," <u>Thin Solid Films</u> , Vol. 321 (1998), pp. 245-250.
<i>SP</i>	C106 Chen <i>et al.</i> , "The Band Model and the Etching Mechanism of Silicon in Aqueous KOH," <u>Journal of the Electrochemical Society</u> , Vol. 142, No. 1 (January 1995), pp. 170-176.
<i>SP</i>	C107 Desmond <i>et al.</i> , "The Effects of Process-Induced Defects on the Chemical Selectivity of Highly Doped Boron Etch Stops in Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 141, No. 1 (January 1994), pp. 178-184.
<i>SP</i>	C108 Ehman <i>et al.</i> , "Morphology of Etch Pits on Germanium Studied by Optical and Scanning Electron Microscopy," <u>Journal of Applied Physics</u> , Vol. 41, No. 7 (June 1970), pp. 2824-2827.
<i>SP</i>	C109 Feijóo <i>et al.</i> , "Etch Stop Barriers in Silicon Produced by Ion Implantation of Electrically Non-Active Species," <u>Journal of the Electrochemical Society</u> , Vol. 139, No. 8 (August 1992), pp. 2309-2313.
<i>SP</i>	C110 Finne <i>et al.</i> , "A Water-Amine-Complexing Agent System for Etching Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 114, No. 9 (September 1967), pp. 965-970.
<i>SP</i>	C111 Fitzgerald, "GeSi/Si Nanostructures," <u>Annual Review of Materials Science</u> , Vol. 25 (1995), pp. 417-454.

EXAMINER

S. S. Liu

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3/2/07

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OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
	C112	Frank, "Orientation-Dependent Dissolution of Germanium," <u>Journal of Applied Physics</u> , Vol. 31, No. 11 (November 1960), pp.1996-1999.							
	C113	Fukatsu, "SiGe-based semiconductor-on-insulator substrate created by low-energy separation-by-implanted-oxygen," <u>Applied Physics Letters</u> , Vol. 72, No. 26 (June 29, 1998), pp. 3485-3487.							
	C114	Ghandi <i>et al.</i> , "Chemical Etching of Germanium," <u>Journal of the Electrochemical Society</u> , Vol. 135, No. 8 (August 1988), pp.2053-2054.							
	C115	Godbey <i>et al.</i> , "A Si _{0.7} Ge _{0.3} strained-layer etch stop for the generation of thin layer undoped silicon," <u>Applied Physics Letters</u> , Vol. 56, No. 4 (January 22, 1990), pp. 373-375.							
	C116	Herzog <i>et al.</i> , "X-Ray Investigation of Boron- and Germanium-Doped Silicon Epitaxial Layers," <u>Journal of the Electrochemical Society</u> , Vol. 131, No. 12 (December 1984), pp.2969-2974.							
	C117	Holmes, "The Orientation Dependence of Etching Effects on Germanium Crystals," <u>Acta Metallurgica</u> , Vol. 7, No. 4 (April 1959), pp. 283-290.							
	C118	Huang <i>et al.</i> , "The Impact of Scaling Down to Deep Submicron on CMOS RF Circuits," <u>IEEE Journal of Solid State Circuits</u> , Vol. 33, No. 7 (July 1998), pp. 1023-1036							
	C119	Hunt <i>et al.</i> , "Highly Selective Etch Stop by Stress Compensation for Thin-Film BESOI," <u>1990 IEEE SOI Technology Conference</u> , (October 2-4, 1990), pp.145-146.							
	C120	Jaccodine, "Use of Modified Free Energy Theorems to Predict Equilibrium Growing and Etching Shapes," <u>Journal of Applied Physics</u> , Vol. 33, No. 8 (August 1962), pp. 2643-2647.							
	C121	Kern, "Chemical Etching of Silicon, Germanium, Gallium, Arsenide, and Gallium Phosphide," <u>RCA Review</u> , Vol. 39 (June 1978), pp. 278-308.							
	C122	Lang <i>et al.</i> , "Bulk Micromachining of Ge for IR Gratings," <u>Journal of Micromechanics and Microengineering</u> , Vol. 6, No.1 (March 1996), pp. 46-48.							
	C123	Leancu <i>et al.</i> , "Anisotropic Etching of Germanium," <u>Sensors and Actuators</u> , A46-47 (1995), pp. 35-37.							
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FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT	ATTY DOCKET NO.: ASC-025DV2C1 APPLICANT(S): Cheng, <i>et al.</i> SERIAL NO.: 10/802,186 FILING DATE: March 17, 2004 GROUP: 2812
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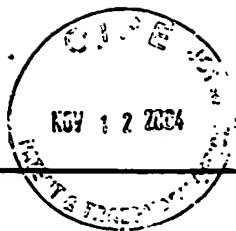
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OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
✓	C124	LeGoues et al., "Relaxation of SiGe thin films grown on Si/SiO ₂ substrates," <u>Applied Physics Letters</u> , Vol. 75, No. 11 (June 1, 1994), pp. 7240-7246.							
✓	C125	Lehmann <i>et al.</i> , "Implanted Carbon: An Effective Etch-Stop in Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 138, No.5 (May 1991), pp. 3-4.							
✓	C126	Narozny et al., "Si/SiGe Heterojunction Bipolar Transistor with Graded GAP SiGe Base Made by Molecular Beam Epitaxy," <u>IEEE IEDM</u> (1988), pp. 562-565.							
✓	C127	Palik <i>et al.</i> , "Ellipsometric Study of the Etch-Stop Mechanism in Heavily Doped Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 132, No. 1 (January 1985), pp. 135-141.							
✓	C128	Palik <i>et al.</i> , "Study of Bias-Dependent Etching of Si in Aqueous KOH," <u>Journal of the Electrochemical Society</u> , Vol. 134, No. 2 (February 1987), pp. 404-409.							
✓	C129	Palik <i>et al.</i> , "Study of the Etch-Stop Mechanism in Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 129, No. 9 (September 1982), pp.2051-2059.							
✓	C130	Petersen, "Silicon as a Mechanical Material," <u>Proceedings of the IEEE</u> , Vol. 70, No. 5 (May 1982), pp. 420-457.							
✓	C131	Powell et al., "New approach to the growth of low dislocation relaxed SiGe material," <u>Applied Physics Letters</u> , Vol. 64, No. 14 (April 4, 1994), pp. 1865-1858.							
✓	C132	Rai-Choudhury <i>et al.</i> , "Doping of Epitaxial Silicon," <u>Journal of Crystal Growth</u> , Vol. 7 (1970), pp. 361-367.							
✓	C133	Raley <i>et al.</i> , "(100) Silicon Etch-Rate Dependence on Boron Concentration in Ethylenediamine - Pyrocatechol-Water Solutions," <u>Journal of the Electrochemical Society</u> , Vol. 131, No. 1 (January 1984), pp. 161-170.							
✓	C134	Seidel et al., "Anisotropic Etching of Crystalline Silicon in Alkaline Solutions," <u>Journal of the Electrochemical Society</u> , Vol. 137, No. 11 (November 1990), pp. 3626-3632.							

EXAMINER	<i>[Signature]</i>	DATE CONSIDERED	3/2/07
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OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
	C135	Senna <i>et al.</i> , "Gallium Doping for Silicon Etch Stop in KOH," <u>Transducers '95/Euroensors IX</u> , the 8 th International Conference on Solid-State Sensors and Actuators and Euroensors IX, Stockholm, Sweden, June 25-29, 1995, pp. 194-195.							
	C136	Shang <i>et al.</i> , "The Development of an Anisotropic Si Etch Process Selective to Ge ₂ Si _{1-x} Underlayers," <u>Journal of the Electrochemical Society</u> , Vol. 141, No. 2 (February 1994), pp. 507-510.							
	C137	Soderbarg, "Fabrication of BESOI-Materials Using Implanted Nitrogen as an Effective Etch Stop Barrier," <u>1989 IEEE SOS/SOI Technology Conference</u> , (October 3-5, 1989), pp. 64.							
	C138	Sundaram <i>et al.</i> , "Electrochemical etching of Silicon by Hydrazine," <u>Journal of the Electrochemical Society</u> , Vol. 140, No. 6 (June 1993), pp. 1592-1597.							
	C139	Sze, "Physics of Semiconductor Devices." (1991).							
	C140	Takagi <i>et al.</i> , "On the Universality of Inversion Layer Mobility in Si MOSFET's: Part I-Effects of Substrate Impurity Concentration," <u>IEEE Transactions on Electron Devices</u> , Vol. 41, No. 12 (December 1994), pp. 2357-2362.							
	C141	Ting <i>et al.</i> , "Monolithic Integration of III-V Materials and Devices on Silicon," Part of the SPIE Conference on Silicon-Based Optoelectronics, San Jose, CA. (January 1999), pp. 19-28.							
	C142	Vol'fson <i>et al.</i> , "Fundamental Absorption Edge of Silicon Heavily Doped with Donor or Acceptor Impurities," <u>Soviet Physics Semiconductors</u> , Vol. 1, No. 3 (September 1967), pp. 327-332.							
	C143	Wu, "Novel Etch-Stop Materials for Silicon Micromachining," Thesis Submitted to the Massachusetts Institute of Technology Department of Materials Science and Engineering on May 9, 1997, pp. 1-62.							
	C144	Yi <i>et al.</i> , "Si _{1-x} Ge _x /Si Multiple Quantum Well Wires Fabricated Using Selective Etching," <u>Materials Research Society Symposium Proceedings</u> , Vol. 379 (1995), pp. 91-96.							

EXAMINER <i>S. J. Lu</i>	DATE CONSIDERED <i>3/2/07</i>
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FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				ATTY DOCKET NO.: ASC-025DV2C1 APPLICANT(S): Cheng, <i>et al.</i> SERIAL NO.: 10/802,186 FILING DATE: March 17, 2004 GROUP: 2812					
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<i>SFL</i>	A236	4,969,031	11/00/1990	Kobayashi <i>et al.</i>					
	A237	5,439,843	08/08/1995	Sakaguchi <i>et al.</i>					
	A238	5,548,128	08/20/1996	Soref <i>et al.</i>					
	A239	5,607,876	03/04/1997	Biegelsen <i>et al.</i>					
	A240	6,489,639	12/03/2002	Hoke <i>et al.</i>					
	A241	6,591,321	07/08/2003	Arimilli <i>et al.</i>			11/09/1999		
	A242	6,597,016	07/22/2003	Yuki <i>et al.</i>			01/13/2000		
	A243	6,646,322	11/11/2003	Fitzgerald			07/16/2001		
	A244	6,674,150	01/06/2004	Takagi <i>et al.</i>			04/23/2002		
	A245	6,677,192	01/13/2004	Fitzgerald			07/16/2001		
	A246	6,703,144	03/09/2004	Fitzgerald			03/18/2003		
	A247	6,703,688	03/09/2004	Fitzgerald			7/16/2001		
	A248	6,737,670	05/18/2004	Cheng <i>et al.</i>			03/07/2003		
	A249	6,750,130	01/07/2001	Fitzgerald			01/07/2001		
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	A251	2003/0215990	11/20/2003	Fitzgerald <i>et al.</i>			03/14/2003		
<i>V</i>	A252	2004/0075149	04/22/2004	Fitzgerald <i>et al.</i>			07/23/2003		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>SFL</i>	B45	61-141116	06/28/1986	JP				N	Y (abstract only)
<i>I</i>	B46	2-210816	08/22/1990	JP				N	Y (abstract only)
<i>V</i>	B47	3-036717	02/18/1991	JP				N	Y
EXAMINER <i>SFL</i>					DATE CONSIDERED <i>3/02/07</i>				

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FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				ATTY DOCKET NO.: ASC-025DV2C1 APPLICANT(S): Cheng, <i>et al.</i> SERIAL NO.: 10/802,186 FILING DATE: March 17, 2004 GROUP: 2812					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
✓	C98	Grillot <i>et al.</i> , "Acceptor diffusion and segregation in $(\text{Al}_x\text{Ga}_{1-x})_{0.5}\text{In}_{0.5}\text{P}$ heterostructures," <u>Journal of Applied Physics</u> , Vol. 91, No. 8 (2002), pp. 4891-4899.							
✓	C99	Halsall <i>et al.</i> , "Electron diffraction and Raman studies of the effect of substrate misorientation on ordering in the AlGaInP system," <u>Journal of Applied Physics</u> , Vol. 85, No. 1 (1999), pp. 199-202.							
✓	C100	Hsu <i>et al.</i> , "Surface morphology of related $\text{Ge}_x\text{Si}_{1-x}$ films," <u>Appl. Phys. Lett.</u> , Vol. 61, No. 11 (1992), pp. 1293-1295							
EXAMINER <i>B. Flu</i>					DATE CONSIDERED <i>3/02/07</i>				

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APPLICANTS: Cheng *et al.*

SERIAL NO.: 10/802,186

FILING DATE: March 17, 2004

GROUP: Not yet assigned

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	

EXAMINER

DATE CONSIDERED

FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTY DOCKET NO.: ASC-025DV2C1 APPLICANTS: Cheng <i>et al.</i> SERIAL NO.: 10/802,186 FILING DATE: March 17, 2004 GROUP: Not yet assigned			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Spl</i>	A1	4,010,045	03/01/1977	Ruehrwein			
	A2	4,704,302	11/03/1987	Bruehl et al.			
	A3	4,710,788	12/01/1987	Dämbkes et al.			
	A4	4,987,462	01/22/1991	Kim et al.			
	A5	4,990,979	02/05/1991	Otto			
	A6	4,997,776	03/05/1991	Haramé et al.			
	A7	5,013,681	05/07/1991	Godbey et al.			
	A8	5,155,571	10/13/1992	Wang et al.			
	A9	5,166,084	11/24/1992	Pfiester			
	A10	5,177,583	01/05/1993	Endo et al.			
	A11	5,202,284	04/13/1993	Kamins et al.			
	A12	5,207,864	05/04/1993	Bhat et al.			
	A13	5,208,182	05/04/1993	Narayan et al.			
	A14	5,212,110	05/18/1993	Pfiester et al.			
	A15	5,221,413	06/22/1993	Brasen et al.			
	A16	5,240,876 A	08/31/1993	Gaul et al.			
	A17	5,241,197	08/31/1993	Murakami et al.			
	A18	5,250,445	10/05/1993	Bean et al.			
	A19	5,285,086	02/08/1994	Fitzgerald			
	A20	5,291,439	03/01/1994	Kauffmann et al.			
	A21	5,298,452	03/29/1994	Meyerson			
	A22	5,310,451	05/10/1994	Tejwani et al.			
	A23	5,316,958	05/31/1994	Meyerson			
	A24	5,346,848	09/13/1994	Gruppen-Shemansky et al.			
	A25	5,374,564	12/20/1994	Bruehl			
	A26	5,399,522	03/21/1995	Ohori			
	A27	5,413,679	05/09/1995	Godbey			
EXAMINER <i>Spl</i>				DATE CONSIDERED 3/2/07			

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INFORMATION DISCLOSURE STATEMENT				APPLICANTS: Cheng <i>et al.</i>			
				SERIAL NO.: 10/802,186			
				FILING DATE: March 17, 2004			
				GROUP: Not yet assigned			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Sph</i>	A28	5,424,243	06/13/1995	Takasaki			
	A29	5,426,069	06/20/1995	Selvakumar et al.			
	A30	5,426,316	06/20/1995	Mohammad			
	A31	5,442,205	08/15/1995	Brasen et al.			
	A32	5,461,243	10/24/1995	Ek et al.			
	A33	5,461,250	10/24/1995	Burghartz et al.			
	A34	5,462,883	10/31/1995	Dennard et al.			
	A35	5,476,813	12/19/1995	Naruse			
	A36	5,479,033	12/26/1995	Baca et al.			
	A37	5,484,664	01/16/1996	Kitahara et al.			
	A38	5,523,243	06/04/1996	Mohammad			
	A39	5,523,592	06/04/1996	Nakagawa et al.			
	A40	5,534,713	07/09/1996	Ismail et al.			
	A41	5,536,361	07/16/1996	Kondo et al.			
	A42	5,540,785	07/30/1996	Dennard et al.			
	A43	5,596,527	01/21/1997	Tomioka et al.			
	A44	5,617,351	04/01/1997	Bertin et al.			
	A45	5,630,905	05/20/1997	Lynch et al.			
	A46	5,659,187	08/19/1997	Legoues et al.			
	A47	5,683,934	11/04/1997	Candelaria			
	A48	5,698,869	12/16/1997	Yoshimi et al.			
	A49	5,714,777	02/03/1998	Ismail et al.			
	A50	5,728,623	03/17/1998	Mori			
	A51	5,739,567	04/14/1998	Wong			
	A52	5,759,898	06/02/1998	Ek et al.			
	A53	5,777,347	07/07/1998	Bartelink			
	A54	5,786,612	07/28/1998	Otani et al.			
EXAMINER <i>Sph</i>				DATE CONSIDERED 3/2/07			

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INFORMATION DISCLOSURE STATEMENT				APPLICANTS: Cheng <i>et al.</i>			
				SERIAL NO.: 10/802,186			
				FILING DATE: March 17, 2004			
				GROUP: Not yet assigned			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>SL</i>	A55	5,786,614	07/28/1998	Chuang et al.			
	A56	5,792,679	08/11/1998	Nakato			
	A57	5,808,344	09/15/1998	Ismail et al.			
	A58	5,847,419	12/08/1998	Imai et al.			
	A59	5,863,830	01/26/1999	Bruel et al.			
	A60	5,877,070	03/02/1999	Goesele et al.			
	A61	5,882,987	03/16/1999	Srikrishnan			
	A62	5,891,769	04/06/1999	Hong et al.			
	A63	5,906,708	05/25/1999	Robinson et al.			
	A64	5,906,951	05/25/1999	Chu et al.			
	A65	5,912,479	06/15/1999	Mori et al.			
	A66	5,943,560	08/24/1999	Chang et al.			
	A67	5,963,817	10/05/1999	Chu et al.			
	A68	5,966,622	10/12/1999	Levine et al.			
	A69	5,993,677	11/30/1999	Biasse et al.			
	A70	5,998,807	12/07/1999	Lustig et al.			
	A71	6,013,134	01/11/2000	Chu et al.			
	A72	6,013,563	01/11/2000	Henley et al.			
	A73	6,020,252	02/01/2000	Aspar et al.			
	A74	6,033,974	03/07/2000	Henley et al.			
	A75	6,033,995	03/07/2000	Muller			
	A76	6,058,044	05/02/2000	Sugiura et al.			
	A77	6,059,895	05/09/2000	Chu et al.			
	A78	6,074,919	06/13/2000	Gardner et al.			
	A79	6,096,590	08/01/2000	Chan et al.			
	A80	6,103,559	08/15/2000	Gardner et al.			
	A81	6,103,597	08/15/2000	Aspar et al.			
EXAMINER <i>SL</i>				DATE CONSIDERED <i>3/2/07</i>			

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GROUP: Not yet assigned

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>SP</i>	A82	6,103,599	08/15/2000	Henley et al.			
	A83	6,107,653	08/22/2000	Fitzgerald			
	A84	6,111,267	08/29/2000	Fischer et al.			
	A85	6,117,750	09/12/2000	Bensahel et al.			
	A86	6,130,453	10/10/2000	Mei, et al.			
	A87	6,133,799	10/17/2000	Favors Jr., et al.			
	A88	6,140,687	10/31/2000	Shimomura et al.			
	A89	6,143,636	11/07/2000	Forbes et al.			
	A90	6,153,495	11/28/2000	Kub et al.			
	A91	6,154,475	11/28/2000	Soref et al.			
	A92	6,160,303	12/12/2000	Fattaruso			
	A93	6,162,688	12/19/2000	Gardner et al.			
	A94	6,162,705	12/19/2000	Henley et al.			
	A95	6,184,111	02/06/2001	Henley et al.			
	A96	6,190,998 B1	02/20/2001	Bruel et al.			
	A97	6,191,007	02/20/2001	Matsui et al.			
	A98	6,191,432	02/20/2001	Sugiyama et al.			
	A99	6,194,722	02/27/2001	Howe et al.			
	A100	6,204,529	03/20/2001	Lung, et al.			
	A101	6,207,977	03/27/2001	Augusto			
	A102	6,210,988	04/03/2001	Howe et al.			
	A103	6,218,677	04/17/2001	Broekaert			
	A104	6,225,192 B1	05/01/2001	Aspar et al.			
	A105	6,232,138	05/15/2001	Fitzgerald et al.			
	A106	6,235,567	05/22/2001	Huang			
<i>✓</i>	A107	6,242,324	06/05/2001	Kub et al.			
<i>✓</i>	A108	6,249,022	06/19/2001	Lin, et al.			

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U.S. PATENT DOCUMENTS							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
✓	A109	6,251,751 B1	06/26/2001	Chu et al.			
✓	A110	6,251,755	06/26/2001	Furukawa et al.			
✓	A111	6,261,929	07/17/2001	Gehrke et al.			
✓	A112	6,266,278	07/24/2001	Harari, et al.			
✓	A113	6,271,551	08/07/2001	Schmitz et al.			
✓	A114	6,271,726	08/07/2001	Fransis et al.			
✓	A115	6,290,804 B1	09/18/2001	Henley et al.			02/20/1998
✓	A116	6,291,321	09/18/2001	Fitzgerald			03/09/1999
✓	A117	6,303,468 B1	10/16/2001	Aspar et al.			10/16/2001
✓	A118	6,313,016	11/06/2001	Kibbel et al.			12/22/1999
✓	A119	6,316,301	11/13/2001	Kant			03/08/200
✓	A120	6,323,108	11/27/2001	Kub et al.			07/27/1999
✓	A121	6,326,667 B1	12/04/2001	Sugiyama et al.			09/08/2000
✓	A122	6,329,063	12/11/2001	Lo et al.			12/11/1998
✓	A123	6,335,546	01/01/2002	Tsuda et al.			07/30/1999
✓	A124	6,339,232	01/15/2002	Takagi			09/20/1999
✓	A125	6,344,417 B1	02/05/2002	Usenko			08/08/2000
✓	A126	6,346,459 B1	02/12/2002	Usenko et al.			02/02/2000
✓	A127	6,350,993	02/26/2002	Chu et al.			03/12/1999
✓	A128	6,352,909 B1	03/05/2002	Usenko			05/26/2000
✓	A129	6,355,493 B1	03/12/2002	Usenko			06/30/2000
✓	A130	6,368,733	04/09/2002	Nishinaga			08/05/1999
✓	A131	6,368,938 B1	04/09/2002	Usenko			06/07/2000
✓	A132	6,369,438 B1	04/09/2002	Sugiyama et al.			12/22/2000
✓	A133	6,372,356	04/16/2002	Thornton et al.			04/28/2000
✓	A134	6,372,593 B1	04/16/2002	Hattori et al.			07/19/2000
✓	A135	6,372,609 B1	04/16/2002	Aga et al.			10/08/1999
EXAMINER <i>S. Lu</i>			DATE CONSIDERED <i>3/2/07</i>				

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INFORMATION DISCLOSURE STATEMENT				APPLICANTS: Cheng <i>et al.</i>			
				SERIAL NO.: 10/802,186			
				FILING DATE: March 17, 2004			
				GROUP: Not yet assigned			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>SH</i>	A136	6,387,829 B1	05/14/2002	Usenko et al.			04/06/2000
	A137	6,391,740 B1	05/21/2002	Cheung et al.			04/28/1999
	A138	6,399,970	06/04/2002	Kubo et al.			09/19/1997
	A139	6,403,975	06/11/2002	Brunner et al.			04/08/1997
	A140	6,407,406	06/18/2002	Tezuka			06/29/1999
	A141	6,410,371 B1	06/25/2002	Yu et al.			02/26/2001
	A142	6,425,951	07/30/2002	Chu et al.			08/06/1999
	A143	6,429,061	08/06/2002	Rim			07/26/2000
	A144	6,445,016 B1	09/03/2002	An et al.			02/28/2001
	A145	6,448,152 B1	09/10/2002	Henley et al.			07/16/2001
	A146	6,455,397 B1	09/24/2002	Belford			11/09/2000
	A147	6,458,672 B1	10/01/2002	Henley et al.			11/02/2000
	A148	6,475,072 B1	11/05/2002	Canaperi et al.			09/29/2000
	A149	6,514,836 B2	02/04/2003	Belford			06/04/2001
	A150	6,515,335 B1	02/04/2003	Christiansen et al.			01/04/2002
	A151	6,521,041	02/18/2003	Wu et al.			04/09/1999
	A152	6,524,935 B1	02/25/2003	Canaperi et al.			09/29/2000
	A153	6,534,381 B2	03/18/2003	Cheung et al.			01/04/2000
	A154	6,555,839	04/29/2003	Fitzgerald et al.			05/16/2001
	A155	6,573,126	06/03/2003	Cheng et al.			08/10/2001
	A156	6,583,015	06/24/2003	Fitzgerald et al.			08/06/2001
	A157	6,583,437 B2	06/24/2003	Mizuno et al.			03/19/2001
	A158	6,593,191	07/15/2003	Fitzgerald			05/16/2001
	A159	6,593,625 B2	07/15/2003	Christiansen et al.			04/03/2002
	A160	6,596,610 B1	07/22/2003	Kuwabara et al.			11/27/2000
<i>V</i>	A161	6,602,613	08/05/2003	Fitzgerald			01/17/2001
<i>V</i>	A162	6,603,156	08/05/2003	Rim			03/31/2001
EXAMINER <i>EJL</i>				DATE CONSIDERED <i>3/2/07</i>			

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APPLICANTS: Cheng *et al.*

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U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>SP</i>	A163	6,607,948 B1	08/19/2003	Sugiyama et al.			08/24/2001
	A164	6,624,047 B1	09/23/2003	Sakaguchi et al.			02/01/2000
	A165	6,624,478 B2	09/23/2003	Anderson et al.			01/30/2002
	A166	6,632,724 B2	10/14/2003	Henley et al.			01/13/2000
	A167	6,635,909 B2	10/21/2003	Clark et al.			03/19/2002
	A168	6,645,831 B1	11/11/2003	Shaheen et al.			05/07/2002
	A169	6,649,492 B2	11/18/2003	Chu et al.			02/11/2002
	A170	6,656,271 B2	12/02/2003	Yonchara et al.			12/03/1999
	A171	6,664,169 B1	12/16/2003	Iwasaki et al.			06/05/2000
	A172	6,677,183 B2	01/13/2004	Sakaguchi et al.			01/31/2002
	A173	6,680,240 B1	01/20/2004	Maszara			06/25/2002
	A174	6,680,260 B2	01/20/2004	Akiyama et al.			09/17/2002
	A175	6,690,043 B1	02/10/2004	Usuda et al.			11/22/2000
	A176	6,706,614 B1	03/16/2004	An et al.			05/15/2002
	A177	6,706,618 B2	03/16/2004	Takisawa et al.			07/29/2002
	A178	6,707,106 B1	03/16/2004	Wristers et al.			10/18/2002
	A179	6,709,903 B2	03/23/2004	Christiansen et al.			04/30/2003
	A180	6,709,909 B2	03/23/2004	Mizuno et al.			05/19/2003
	A181	6,713,326 B2	03/30/2004	Cheng et al.			03/04/2003
	A182	2001/0003364	06/14/2001	Sugawara et al.			12/08/2000
	A183	2001/0007789 A1	07/12/2001	Aspar et al.			02/26/2001
	A184	2002/0043660	04/18/2002	Yamazaki et al.			06/25/2001
	A185	2002/052084	05/02/2002	Fitzgerald			05/16/2001
	A186	2002/096717	07/25/2002	Chu et al.			01/25/2001
	A187	2002/0100942	08/01/2002	Fitzgerald et al.			08/01/2002
	A188	2002/0123167	09/05/2002	Fitzgerald			07/16/2001
	A189	2002/0123183	09/05/2002	Fitzgerald			07/16/2001

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				SERIAL NO.: 10/802,186			
				FILING DATE: March 17, 2004			
				GROUP: Not yet assigned			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>SP</i>	A190	2002/0123197	09/05/2002	Fitzgerald et al.			06/19/2001
	A191	2002/0125471	09/12/2002	Fitzgerald et al.			12/04/2001
	A192	2002/0125497	09/12/2002	Fitzgerald			07/16/2001
	A193	2002/0168864	11/14/2002	Cheng et al.			04/04/2002
	A194	2003/0003679	01/02/2003	Doyle et al.			06/29/2001
	A195	2003/0013305 A1	01/16/2003	Sugii et al.			6/17/2002
	A196	2003/0013323	01/16/2003	Hammond et al.			6/14/2002
	A197	2003/0025131	02/06/2003	Lee et al.			08/02/2002
	A198	2003/0034529	02/20/2003	Fitzgerald et al.			10/08/2002
	A199	2003/0057439	03/27/2003	Fitzgerald			08/09/2002
	A200	2003/0077867	04/04/2003	Fitzgerald			07/16/2001
	A201	2003/0102498	06/05/2003	Braithwaite et al.			09/24/2002
	A202	2003/0119280 A1	06/26/2003	Lee et al.			12/02/2002
	A203	2003/0127646 A1	07/10/2003	Christiansen et al.			12/18/2002
	A204	2003/0139000 A1	07/24/2003	Bedell et al.			01/23/2002
	A205	2003/0157787 A1	08/21/2003	Murthy et al.			02/21/2002
	A206	2003/0160300 A1	08/28/2003	Takenaka et al.			02/24/2003
	A207	2003/0168654 A1	09/11/2003	Cheng et al.			03/07/2003
	A208	2003/0178681 A1	09/25/2003	Clark et al.			04/02/2003
	A209	2003/0189229 A1	10/09/2003	Mouli			04/05/2002
	A210	2003/0199126 A1	10/23/2003	Chu et al.			04/23/2002
	A211	2003/0201458 A1	10/30/2003	Clark et al.			05/16/2003
	A212	2003/0203600 A1	10/30/2003	Chu et al.			06/05/2003
	A213	2003/0207127 A1	11/06/2003	Murthy et al.			05/30/2003
	A214	2003/0218189 A1	11/27/2003	Christiansen et al.			11/19/2002
	A215	2003/0219957 A1	11/27/2003	Kuwabara et al.			05/29/2003
<i>✓</i>	A216	2003/0227036 A1	12/11/2003	Sugiyama et al.			02/21/2003
EXAMINER <i>SP</i>				DATE CONSIDERED <i>7/2/07</i>			

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INFORMATION DISCLOSURE STATEMENT

ATTY DOCKET NO.: ASC-025DV2C1

APPLICANTS: Cheng *et al.*

SERIAL NO.: 10/802,186

FILING DATE: March 17, 2004

GROUP: Not yet assigned

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>SP</i>	A217	2003/0227057	12/01/2003	Lochtefeld et al.			10/04/2002
	A218	2003/0230778 A1	12/18/2003	Park et al.			01/30/2003
	A219	2003/0232467 A1	12/18/2003	Anderson et al.			05/29/2003
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	A230	2004/0041210 A1	03/04/2004	Mouli			09/02/2003
	A231	2004/0048091 A1	03/11/2004	Sato et al.			09/04/2003
	A232	2004/0048454 A1	03/11/2004	Sakaguchi			09/04/2003
	A233	2004/0051140 A1	03/18/2004	Bhattacharyya			09/12/2002
<i>✓</i>	A234	2004/0053477 A1	03/18/2004	Ghyselen et al.			07/09/2003

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B1	41 01 167	07/23/1992	DE				No	No
	B2	0 514 018	11/19/1992	EP				No	Yes
	B3	0 587 520	03/16/1994	EP				No	Yes
	B4	0 683 522	11/22/1995	EP				No	Yes
	B5	0 828 296	03/11/1998	EP				No	Yes
	B6	0 829 908	03/18/1998	EP				No	Yes
	B7	0 838 858	04/29/1998	EP				No	No

EXAMINER

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DATE CONSIDERED

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				GROUP: Not yet assigned					
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLAS S	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B8	1 020 900	07/19/2000	EP				No	Yes
	B9	1 174 928	01/23/2002	EP				No	Yes
	B10	2 342 777	04/19/2000	GB				Yes	Yes
	B11	4-307974	10/30/1992	JP				No	No
	B12	5-166724	07/03/1993	JP				No	Abstract Only
	B13	6-177046	06/24/1994	JP				No	Abstract Only
	B14	7-106446	04/21/1995	JP				No	No
	B15	7-240372	09/12/1995	JP				No	Abstract Only
	B16	10-270685	10/09/1998	JP				No	Yes
	B17	11-233744	08/27/1999	JP				No	No
	B18	2000-021783	01/21/2000	JP				No	Yes
	B19	2000-31491	01/28/2000	JP				No	No
	B20	2001319935	05/11/2000	JP				Yes	Yes
	B21	2002-076334	03/15/2002	JP				No	Yes
	B22	2002-164520	06/07/2002	JP				No	Yes
	B23	2002-289533	10/04/2002	JP				No	Yes
	B24	WO 98/59365	12/30/1998	PCT				No	Yes
	B25	WO 99/53539	10/21/1999	PCT				No	Yes
	B26	WO 00/48239	08/17/2000	PCT				No	Yes
	B27	WO 01/54202	07/26/2001	PCT				No	Yes
	B28	WO 01/99169A2	12/27/2001	PCT				No	Yes
	B29	WO 02/15244 A2	02/21/2002	PCT				No	Yes
	B30	WO 02/27783 A1	04/04/2002	PCT				No	Yes
	B31	WO 02/071495A1	09/12/2002	PCT				No	Yes
EXAMINER				DATE CONSIDERED					

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	B33	WO 00/54338	09/14/2000	WO				No	Yes
	B34	WO 01/022482	03/29/2001	WO				No	Yes
	B35	WO 01/93338	12/06/2001	WO				No	Yes
	B36	WO 02/13262	02/14/2002	WO				No	Yes
	B37	WO 02/47168	06/13/2002	WO				No	Yes
	B38	WO 02/071488	09/12/2002	WO				No	Yes
	B39	WO 02/071491	09/12/2002	WO				No	Yes
	B40	WO 04/006311 A2	01/15/2004	WO			07/09/2003		YES
	B41	WO 04/006326 A1	01/15/2004	WO			07/09/2003		YES
	B42	WO 04/006327 A2	01/15/2004	WO			07/09/2003		YES
	B43	WO 04/019403 A2	03/04/2004	WO			08/26/2003		YES
	B44	WO 04/019404 A2	03/04/2004	WO			08/26/2003		YES
OTHER ART, JOURNAL ARTICLES, ETC.									
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	C1	"2 Bit/Cell EEPROM Cell Using Band to Band Tunneling for Data Read-Out," IBM Technical Disclosure Bulletin, Vol. 35, No. 4B (September 1992) pp. 136-140.							
	C2	Armstrong et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEDM Technical Digest</u> (1995) pp. 761-764.							
	C3	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices", Ph.D Thesis, Massachusetts Institute of Technology (1999) pp. 1-154.							
	C4	Augusto et al., "Proposal for a New Process Flow for the Fabrication of Silicon-Based Complementary MOD-MOSFETs without Ion Implantation," <u>Thin Solid Films</u> , Vol. 294, No. 1-2 (1997) pp. 254-258.							
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	C6	Borenstein et al., "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," <u>Proceedings of the 1999 12th IEEE International Conference on Micro Electro Mechanical Systems (MEMS)</u> (January 17-21, 1999) pp. 205-210.
	C7	Bouillon et al., "Search for the optimal channel architecture for 0.18/0.12 μm bulk CMOS Experimental study," <u>IEEE</u> (1996) pp. 21.2.1-21.2.4.
	C8	Bruel et al., "@SMART CUT: A Promising New SOI Material Technology," <u>Proceedings 1995 IEEE International SOI Conference</u> (October 1995) pp. 178-179.
	C9	Bruel, "Silicon on Insulator Material Technology," <u>Electronic Letters</u> , Vol. 13, No. 14 (July 6, 1995) pp. 1201-1202.
	C10	Bufler et al., "Hole transport in strained $\text{Si}_{1-x}\text{Ge}_x$ alloys on $\text{Si}_{1-y}\text{Ge}_y$ substrates," <u>Journal of Applied Physics</u> , Vol. 84, No. 10 (November 15, 1998) pp. 5597-5602.
	C11	Burghartz et al., "Microwave Inductors and Capacitors in Standard Multilevel Interconnect Silicon Technology," <u>IEEE Transactions on Microwave Theory and Techniques</u> , Vol. 44, No. 1 (January 1996) pp. 100-104.
	C12	Carlin et al., "High Efficiency GaAs-on-Si Solar Cells with High Voc Using Graded GeSi Buffers," <u>IEEE</u> (2000) pp. 1006-1011
	C13	Chang et al., "Selective Etching of SiGe/Si Heterostructures," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991) pp. 202-204.
	C14	Cheng et al., "Electron Mobility Enhancement in Strained Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 7 (July 2001) pp. 321-323.
	C15	Cheng et al., "Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer," <u>Journal of Electronic Materials</u> , Vol. 30, No. 12 (2001) pp. L37-L39.
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	C20	Feijoo et al., "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," <u>Journal of Electronic Materials</u> , Vol. 23, No. 6 (June 1994) pp. 493-496.
	C21	Fischetti et al., "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," <u>J. Appl. Phys.</u> , Vol. 80, No. 4 (August 15, 1996) pp. 2234-2252.
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	C22	Fischetti, "Long-range Coulomb interactions in small Si devices. Part II. Effective electron mobility in thin-oxide structures," <u>Journal of Applied Physics</u> , Vol. 89, No. 2 (January 15, 2001) pp. 1232-1250.	
	C23	Fitzgerald et al., "Dislocation dynamics in relaxed graded composition semiconductors," <u>Materials Science and Engineering B67</u> (1999) pp. 53-61.	
	C24	Fitzgerald et al., "Relaxed Ge _x Si _{1-x} structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," AT&T Bell Laboratories, Murray Hill, NJ 07974 (1992) <u>American Vacuum Society</u> , pp. 1807-1819.	
	C25	Fitzgerald et al., "Totally Relaxed Ge _x Si _{1-x} Layers with Low Threading Dislocation Densities Grown on Si Substrates," <u>Applied Physics Letters</u> , Vol. 59, No. 7 (August 12, 1991) pp. 811-813.	
	C26	Garone et al., "Silicon vapor phase epitaxial growth catalysis by the presence of germane," <u>Applied Physics Letters</u> , Vol. 56, No. 13 (March 26, 1990) pp. 1275-1277.	
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	C28	Gray and Meyer, "Phase-Locked Loops", <u>Analysis and Design of Analog Integrated Circuits</u> (1984) pp. 605-632.	
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	C38	Huang et al., "The Impact of Scaling Down to Deep Submicron on CMOS RF Circuits", <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 7, July, 1998, pp. 1023-1036.	
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	C40	Ishikawa et al., "Creation of Si-Ge-based SIMOX structures by low energy oxygen implantation," <u>Proceedings 1997 IEEE International SOI Conference</u> (October 1997) pp. 16-17.	
	C41	Ishikawa et al., "SiGe-on-insulator substrate using SiGe alloy grown Si(001)," <u>Applied Physics Letters</u> , Vol. 75, No. 7 (August 16, 1999) pp. 983-985.	
	C42	Ismail et al., "Modulation-doped n-type Si/SiGe with inverted interface," <u>Appl. Phys. Lett.</u> , Vol. 65, No. 10 (September 5, 1994) pp. 1248-1250.	
	C43	Ismail, "Si/SiGe High-Speed Field-Effect Transistors," <u>Electron Devices Meeting, Washington, D.C.</u> (December 10, 1995) pp. 20.1.1-20.1.4.	
	C44	Kearney et al., "The effect of alloy scattering on the mobility of holes in a Si _{1-x} Ge _x quantum well," <u>Semicond. Sci Technol.</u> , Vol. 13 (1998) pp. 174-180.	
	C45	Kim et al., "A Fully Integrated 1.9-GHz CMOS Low-Noise Amplifier," <u>IEEE Microwave and Guided Wave Letters</u> , Vol. 8, No. 8 (August 1998) pp. 293-295.	
	C46	Koester et al., "Extremely High Transconductance Ge/Si _{0.4} Ge _{0.6} p-MODFET's Grown by UHV-CVD," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 3 (March 2000) pp. 110-112.	
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	C51	Kuznetsov et al., "Technology for high-performance n-channel SiGe modulation-doped field-effect transistors," <u>J. Vac. Sci. Technol., B</u> 13(6) (November/December 1995) pp. 2892-2896.	
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	C53	Larson, "Integrated Circuit Technology Options for RFIC's - Present Status and Future Directions", <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 3, March 1998, pp. 387-399.	
	C54	Lee et al., "CMOS RF Integrated Circuits at 5 GHz and Beyond", <u>Proceedings of the IEEE</u> , Vol. 88, No. 10 (October 2000) pp. 1560-1571.	
	C55	Lee et al., "Strained Ge channel p-type metal-oxide-semiconductor field-effect transistors grown on Si _{1-x} Ge _x /Si virtual substrates," <u>Applied Physics Letters</u> , Vol. 79, No. 20 (November 12, 2001) pp. 3344-3346.	
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	C62	Maiti et al., "Strained-Si heterostructure field effect transistors," <u>Semicond. Sci. Technol.</u> , Vol. 13 (1998) pp. 1225-1246.	
	C63	Maszara, "Silicon-On-Insulator by Wafer Bonding: A Review," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991) pp. 341-347.	
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	C68	Nayak et al., "High-Mobility Strained-Si PMOSFET's"; <u>IEEE Transactions on Electron Devices</u> , Vol. 43, No. 10 (October 1996) pp. 1709-1716.	
	C69	O'Neill et al., "SiGe Virtual substrate N-channel heterojunction MOSFETs," <u>Semicond. Sci. Technol.</u> , Vol. 14 (1999) pp. 784-789.	
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	C71	Papananos, "Low Noise Amplifiers in MOS Technologies," and "Low Noise Tuned-LC Oscillator," <u>Radio-Frequency Microelectronic Circuits for Telecommunication Applications</u> (1999) pp. 115-117, 188-193.	
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EXAMINER		DATE CONSIDERED	

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